

CMOS Hex 'D'-Type Flip-Flop

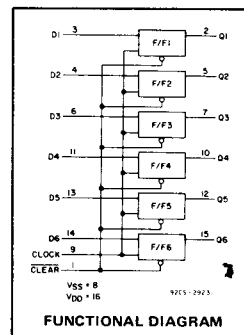
High-Voltage Types (20-Volt Rating)

■ CD40174B consists of six identical 'D'-type flip-flops having independent DATA inputs. The CLOCK and CLEAR inputs are common to all six units. Data is transferred to the Q outputs on the positive-going transition of the clock pulse. All six flip-flops are simultaneously reset by a low level on the CLEAR input.

The CD40174B types are supplied in 16-lead hermetic dual-in-line ceramic packages (D and F suffixes), 16-lead dual-in-line plastic packages (E suffix), and in chip form (H suffix).

Features:

- 5-V, 10-V, and 15-V parametric rating
- Standardized symmetrical output characteristics
- 100% tested for quiescent current at 20 V
- Maximum input current of 1 μ A at 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- Noise margin (over full package-temperature range): 1 V at $V_{DD} = 5$ V
2 V at $V_{DD} = 10$ V
2.5 V at $V_{DD} = 15$ V
- Meets all requirements of JEDEC Tentative Standard No. 13A, "Standard Specifications for Description of 'B' Series CMOS Devices"



Applications:

- Shift Registers
- Buffer/Storage Registers
- Pattern Generators

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, (V_{DD})

Voltages referenced to V_{SS} Terminal) -0.5V to +20V

INPUT VOLTAGE RANGE, ALL INPUTS -0.5V to $V_{DD} + 0.5$ V

DC INPUT CURRENT, ANY ONE INPUT ± 10 mA

POWER DISSIPATION PER PACKAGE (P_D):

For $T_A = -55^\circ\text{C}$ to $+100^\circ\text{C}$ 500mW

For $T_A = +100^\circ\text{C}$ to $+125^\circ\text{C}$ Derate Linearity at 12mW/ $^\circ\text{C}$ to 200mW

DEVICE DISSIPATION PER OUTPUT TRANSISTOR

For $T_A = \text{FULL PACKAGE-TEMPERATURE RANGE (All Package Types)}$ 100mW

OPERATING-TEMPERATURE RANGE (T_A) -55°C to $+125^\circ\text{C}$

STORAGE TEMPERATURE RANGE (T_{stg}) -65°C to $+150^\circ\text{C}$

LEAD TEMPERATURE (DURING SOLDERING):

At distance 1/16 $\pm$ 1/32 inch (1.59 $\pm$ 0.79mm) from case for 10s max $+265^\circ\text{C}$

TRUTH TABLE FOR 1 OF 6 FLIP-FLOPS

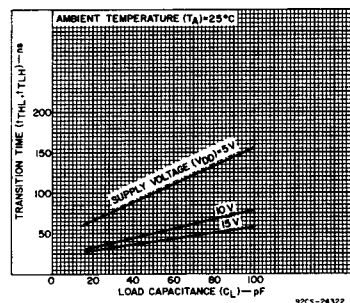
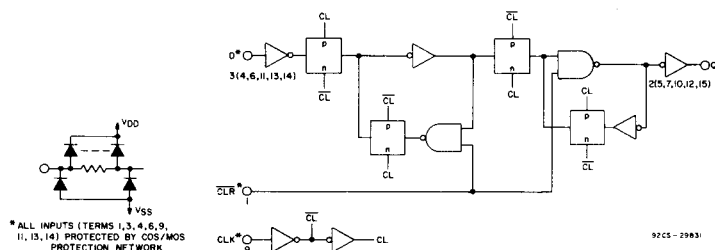
INPUTS			OUTPUT
CLOCK	DATA	CLEAR	Q
	0	1	0
	1	1	1
	X	1	NC
X	X	0	0

1 = High Level

0 = Low Level

X = Don't Care

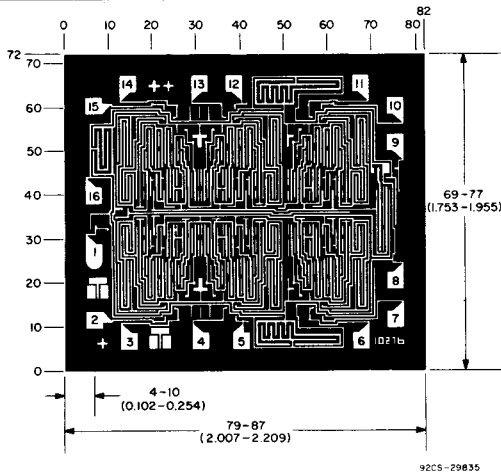
NC = No Change



CD40174B Types

RECOMMENDED OPERATING CONDITIONS at $T_A = 25^\circ\text{C}$, Except as Noted.
For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

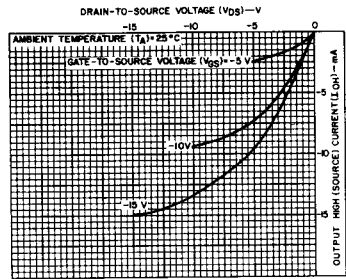
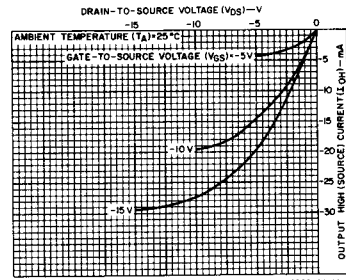
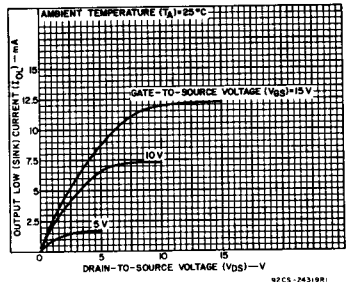
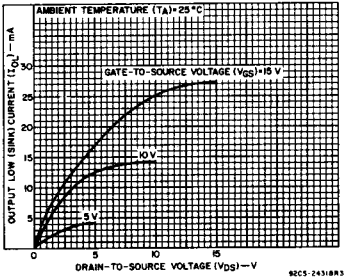
CHARACTERISTIC	V_{DD} (V)	LIMITS		UNITS
		Min.	Max.	
Supply-Voltage Range (For T_A = Full Package-Temperature Range)	—	3	18	V
Data Setup Time, t_{SU}	5	40	—	ns
	10	20	—	
	15	10	—	
Data Hold Time, t_H	5	80	—	ns
	10	40	—	
	15	30	—	
Clock Input Frequency, f_{CL}	5	—	3.5	MHz
	10	dc	6	
	15	—	8	
Clock Input Rise or Fall Time, t_{rCL} , t_{fCL}	5	—	15	μs
	10	—	15	
	15	—	15	
Clock Input Pulse Width, t_{WL} , t_{WH}	5	130	—	ns
	10	60	—	
	15	40	—	
Clear Pulse Width, t_{WL}	5	100	—	ns
	10	50	—	
	15	40	—	
Clear Removal Time, t_{REM}	5	0	—	ns
	10	0	—	
	15	0	—	



Dimensions and pad layout for CD40174BH.

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

The photographs and dimensions of each CMOS chip represent a chip when it is part of the wafer. When the wafer is separated into individual chips, the angle of cleavage may vary with respect to the chip face for different chips. The actual dimensions of the isolated chip, therefore, may differ slightly from the nominal dimensions shown. The user should consider a tolerance of ± 3 mils to ± 16 mils applicable to the nominal dimensions shown.



CD40174B Types

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)								UNITS
	V _O (V)	V _{IN} (V)	V _{DD} (V)	-55	-40	+85	+125	+25				
								Min.	Typ.	Max.		
Quiescent Device Current, I _{DD} Max.	—	0,5	5	1	1	30	30	—	0.02	1	μA	
	—	0,10	10	2	2	60	60	—	0.02	2		
	—	0,15	15	4	4	120	120	—	0.02	4		
	—	0,20	20	20	20	600	600	—	0.04	20		
Output Low (Sink) Current I _{OL} Min.	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	—	mA	
	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	—		
	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	—		
Output High (Source) Current, I _{OH} Min.	4.6	0,5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	—	mA	
	2.5	0,5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	—		
	9.5	0,10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	—		
	13.5	0,15	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8	—		
Output Voltage: Low-Level, V _{OL} Max.	—	0,5	5	0.05				—	0	0.05	V	
	—	0,10	10	0.05				—	—	0.05		
	—	0,15	15	0.05				—	0	0.05		
Output Voltage: High-Level, V _{OH} Min.	—	0,5	5	4.95				4.95	5	—	V	
	—	0,10	10	9.95				9.95	10	—		
	—	0,15	15	14.95				14.95	15	—		
Input Low Voltage, V _{IL} Max.	0.5,4.5	—	5	1.5				—	—	1.5	V	
	1,9	—	10	3				—	—	3		
	1.5,13.5	—	15	4				—	—	4		
Input High Voltage, V _{IH} Min.	0.5,4.5	—	5	3.5				3.5	—	—	V	
	1,9	—	10	7				7	—	—		
	1.5,13.5	—	15	11				11	—	—		
Input Current I _{IN} Max.	—	0,18	18	±0.1	±0.1	±1	±1	—	±10 ⁻⁵	±0.1	μA	

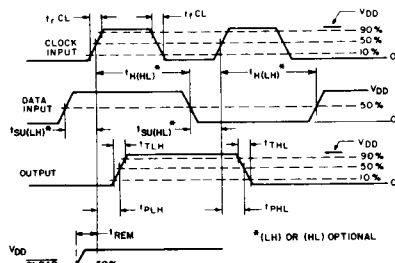


Fig. 10—Definition of setup, hold, propagation delay, and removal times.

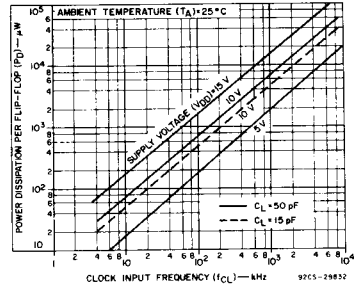


Fig. 7—Typical dynamic power dissipation as a function of CLOCK frequency.

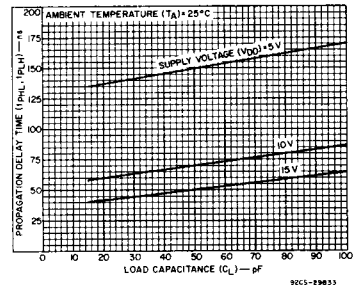


Fig. 8—Typical propagation delay time (CLOCK to OUTPUT) as a function of load capacitance.

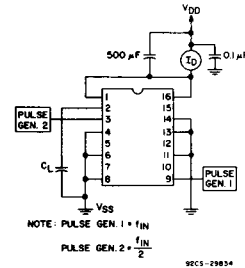


Fig. 9—Dynamic power dissipation test circuit.

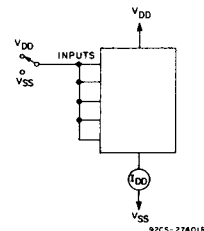


Fig. 11—Quiescent device current test circuit.

CD40174B Types

DYNAMIC ELECTRICAL CHARACTERISTICS at $T_A = 25^\circ\text{C}$;
Input $t_r, t_f = 20\text{ ns}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ k}\Omega$

CHARACTERISTIC	TEST CONDITIONS V_{DD} (V)	LIMITS			UNITS
		Min.	Typ.	Max.	
Propagation Delay Time Clock to Output, t_{PHL}, t_{PLH}	5	—	150	300	ns
	10	—	70	140	
	15	—	50	100	
Clear to Output, t_{PHL}	5	—	100	200	ns
	10	—	50	100	
	15	—	40	80	
Transition Time, t_{THL}, t_{TLH}	5	—	100	200	ns
	10	—	50	100	
	15	—	40	80	
Minimum Pulse Width, Clock, t_{WL}, t_{WH}	5	—	65	130	ns
	10	—	30	60	
	15	—	20	40	
Clear, t_{WL}	5	—	50	100	ns
	10	—	25	50	
	15	—	20	40	
Minimum Data Setup Time, t_{SU}	5	—	20	40	ns
	10	—	10	20	
	15	—	0	10	
Minimum Data Hold Time, t_H	5	—	40	80	ns
	10	—	20	40	
	15	—	15	30	
Maximum Clock Frequency, f_{CL}	5	3.5	7	—	MHz
	10	6	12	—	
	15	8	16	—	
Maximum Clock Rise or Fall Time, t_{rCL}, t_{fCL}	5	15	—	—	μs
	10	15	—	—	
	15	15	—	—	
Input Capacitance, C_{IN} Clear	—	—	25	40	pF
	All other	—	5	7.5	
Minimum Clear Removal Time, t_{REM}	5	—	-40	0	ns
	10	—	-15	0	
	15	—	-10	0	

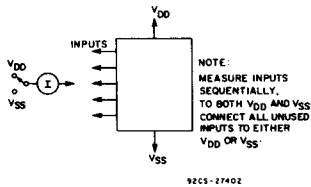


Fig. 12 – Input current test circuit.

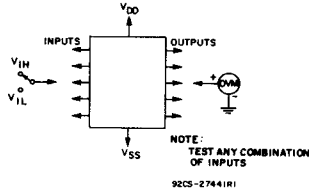


Fig. 13 – Input voltage test circuit.

TERMINAL ASSIGNMENT

